

CMLD3003DO
SURFACE MOUNT
PICOmini™
DUAL, ISOLATED, OPPOSING
LOW LEAKAGE SILICON
SWITCHING DIODES



MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
 Average Rectified Current
 Continuous Forward Current
 Peak Repetitive Forward Current
 Forward Surge Current, $t_p=1 \mu\text{sec}$.
 Forward Surge Current, $t_p=1 \text{ sec}$.
 Power Dissipation
 Operating and Storage
 Junction Temperature
 Thermal Resistance

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD3003DO type contains Two (2) Isolated Opposing Configuration, Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a PICOMini™ surface mount package. These devices are designed for switching applications requiring extremely low leakage.

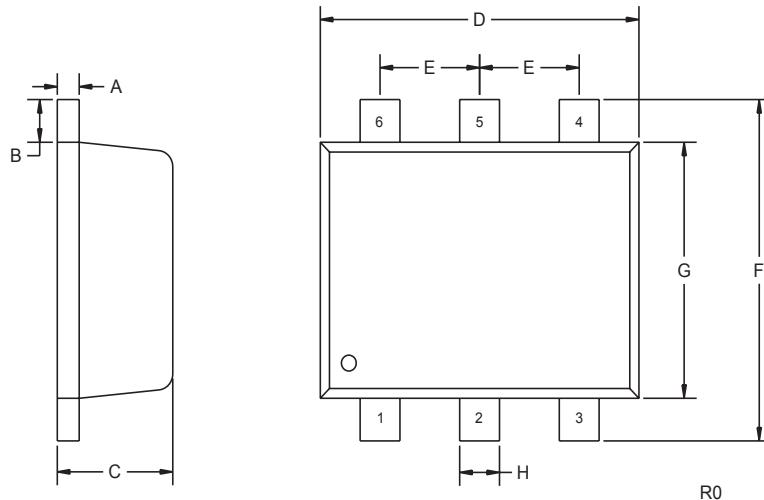
MARKING CODE: C30

SYMBOL	UNITS
V_R	V
I_O	mA
I_F	mA
I_{FRM}	mA
I_{FSM}	A
I_{FSM}	A
P_D	mW
T_J, T_{stg}	${}^\circ\text{C}$
Θ_{JA}	${}^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=125\text{V}$		1.0	nA
I_R	$V_R=125\text{V}, T_A=150^\circ\text{C}$		3.0	μA
I_R	$V_R=180\text{V}$		10	nA
I_R	$V_R=180\text{V}, T_A=150^\circ\text{C}$		5.0	μA
BV_R	$I_R=5.0\mu\text{A}$	200		V
V_F	$I_F=1.0\text{mA}$	0.62	0.72	V
V_F	$I_F=10\text{mA}$	0.72	0.83	V
V_F	$I_F=50\text{mA}$	0.80	0.89	V
V_F	$I_F=100\text{mA}$	0.83	0.93	V
V_F	$I_F=200\text{mA}$	0.87	1.10	V
V_F	$I_F=300\text{mA}$	0.90	1.15	V
C_T	$V_R=0, f=1 \text{ MHz}$		4.0	pF

SOT-563 CASE - MECHANICAL OUTLINE



LEAD CODE:

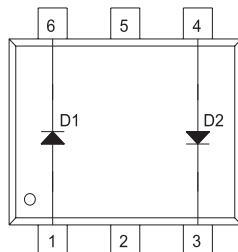
- 1) ANODE D1
- 2) NC
- 3) CATHODE D2
- 4) ANODE D2
- 5) NC
- 6) CATHODE D1

MARKING CODE: C30

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

Dual Opposing Configuration



R0 (07-June 2004)